

## **INCHANGE SEMICONDUCTOR**

# isc N-Channel MOSFET Transistor

## IRFSL4410

pin 1, Gate 2, Drain

3, Source

3

2

D(2)

### • FEATURES

- Static drain-source on-resistance: RDs(on) ≤10mΩ
- Enhancement mode
- Fast Switching Speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

· reliable device for use in a wide variety of applications

#### ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C) SYMBOL PARAMETER VALUE UNIT Voss **Drain-Source Voltage** 100 V V<sub>GS</sub> Gate-Source Voltage $\pm 20$ V **Drain Current-Continuous** 88 А $I_D$ Drain Current-Single Pulsed 380 А **I**DM Total Dissipation @Tc=25°C $P_D$ 2001 W Tj Max. Operating Junction Temperature 175 °C Storage Temperature -55~175 °C Tstg THERMAL CHARACTERISTICS

-	2.5	TO-262 package				
	D1					
		mm		]		
DI	M	MIN	MAX	1		
A	0	4.37	4.77	1		
A		1.22	1.42			
A	2	2.47	2.87	Ī		
ь	<b>7</b> 00	0.70	0.97			
Ь	2	1.17	1.42			
c		0.28	0.53	1		
D	ě	23.20	24.02			
D	1	8.38	8.90			
D	2	6.00				
E	5	9.90	10.39	1		
E	4	7.30		1		
e		2.5	4BSC			
G		1.25	1.50	]		
H	2	() <del></del>	1.31	1		
L	1	13.34	14.10			
L	1	3.30	4.06			

0.95 1.15

L3

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.611	°C/W

1



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## ELECTRICAL CHARACTERISTICS

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID =250 μ A	100			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID =150 μ A	2.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =58A			10.0	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V			±0.2	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V; V <sub>GS</sub> = 0V			20	μA
V <sub>SD</sub>	Diode forward voltage	Is=58A, V <sub>GS</sub> = 0 V			1.3	V

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